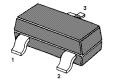
SILICON EPITAXIAL PLANAR DIODE

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance





Marking Code: 5D SOT-23 Plastic Package

Applications

• Ultra high speed switching application

Absolute Maximum Ratings ($T_a = 25 \, ^{\circ}C$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	Io	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Surge Current (10 ms)	I _{FSM}	2	А
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 80 \text{ V}$	I _R	0.5	μΑ
Total Capacitance at $V_R = 0$, $f = 1$ MHz	Ст	3	pF
Reverse Recovery Time at I _F = 10 mA	t _{rr}	4	ns







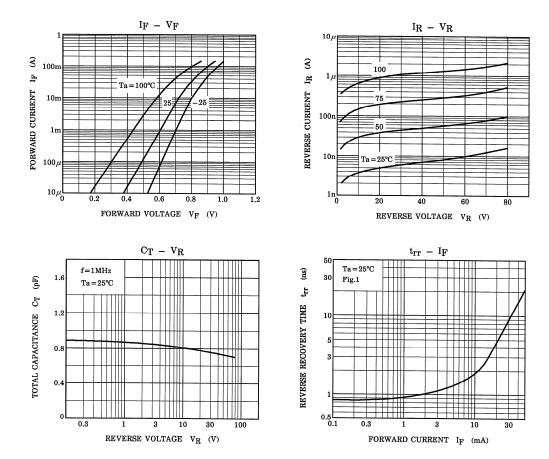
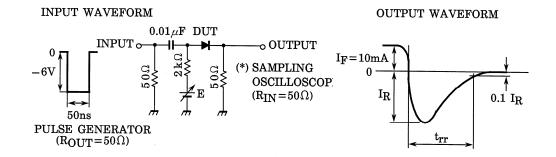


Fig.1 Reverse recovery time (t_{rr}) test circuit





SEMTECH ELECTRONICS LTD.

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